MICROCHIP

28C64A

64K (8K x 8) CMOS EEPROM

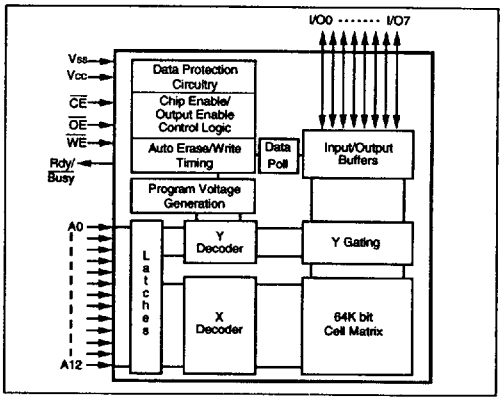
FEATURES

- Fast Read Access Time—150 ns
- CMOS Technology for Low Power Dissipation
  - — 30 mA Active
  - — 100 µA Standby
- Fast Byte Write Time—200 µs or 1 ms
- Data Retention >10 years
- High Endurance - Minimum 10^4 Erase/Write Cycles
- Automatic Write Operation
  - — Internal Control Timer
  - — Auto-Clear Before Write Operation
  - — On-Chip Address and Data Latches
- Data Polling
- Ready/Busy
- Chip Clear Operation
- Enhanced Data Protection
  - — Vcc Detector
  - — Pulse Filter
  - — Write Inhibit
- Electronic Signature for Device Identification
- 5-Volt-Only Operation
- Organized 8Kx8 JEDEC Standard Pinout
  - — 28-pin Dual-In-Line Package
  - — 32-pin Chip Carrier (Leadless or Plastic)
  - — 28-pin Thin Small Outline Package (TSOP) 8x20mm
  - — 28-pin Very Small Outline Package (VSOP) 8x13.4mm
- Available for Extended Temperature Ranges:
  - — Commercial: 0°C to 70°C

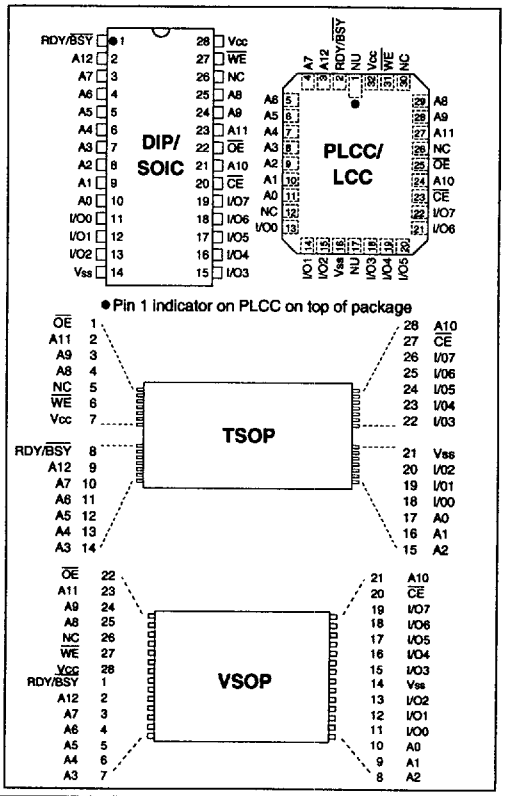
DESCRIPTION

The Microchip Technology Inc. 28C64A is a CMOS 64K non-volatile electrically Erasable PROM. The 28C64A is accessed like a static RAM for the read or write cycles without the need of external components. During a "byte write", the address and data are latched internally, freeing the microprocessor address and data bus for other operations. Following the initiation of write cycle, the device will go to a busy state and automatically clear and write the latched data using an internal control timer. To determine when the write cycle is complete, the user has a choice of monitoring the Ready/Busy output or using Data polling. The Ready/Busy pin is an open drain output, which allows easy configuration in wired-or systems. Alternatively, Data polling allows the user to read the location last written to when the write operation is complete. CMOS design and processing enables this part to be used in systems where reduced power consumption and reliability are required. A complete family of packages is offered to provide the utmost flexibility in applications.

BLOCK DIAGRAM



PIN CONFIGURATION



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ELECTRICAL CHARACTERISTICS

MAXIMUM RATINGS*

Vcc and input voltages w.r.t. Vss ..... -0.6V to + 6.25V
Voltage on $\overline{OE}$ w.r.t. Vss ..... -0.6V to +13.5V
Voltage on A9 w.r.t. Vss ..... -0.6V to +13.5V
Output Voltage w.r.t. Vss ..... -0.6V to Vcc+0.6V
Storage temperature ..... -65°C to 125°C
Ambient temp. with power applied ..... -50°C to 95°C

*Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

PIN FUNCTION TABLE

Name	Function
A0 - A12	Address Inputs
$\overline{CE}$	Chip Enable
$\overline{OE}$	Output Enable
$\overline{WE}$	Write Enable
I/O0 - I/O7	Data Inputs/Outputs
RDY/$\overline{Busy}$	Ready/$\overline{Busy}$
Vcc	+5V Power Supply
Vss	Ground
NC	No Connect; No Internal Connection
NU	Not Used; No External Connection is Allowed

READ / WRITE OPERATION
DC Characteristics

Vcc = +5V ±10%
Commercial (C): Tamb= 0°C to 70°C
Industrial (I): Tamb= -40°C to 85°C

Parameter	Status	Symbol	Min	Max	Units	Conditions
Input Voltages	Logic "1" Logic "0"	V_{IH} V_{IL}	2.0 -0.1	Vcc+1 0.8	V V	
Input Leakage	—	I_{LI}	-10	10	µA	V_{IN} = -0.1V to Vcc+1
Input Capacitance	—	C_{IN}	—	10	pF	V_{IN} = 0V; Tamb = 25°C; f = 1 MHz (Note 2)
Output Voltages	Logic "1" Logic "0"	V_{OH} V_{OL}	2.4	 0.45	V V	I_{OH} = -400 µA I_{OL} = 2.1 mA
Output Leakage	—	I_{LO}	-10	10	µA	V_{OUT} = -0.1V to Vcc+0.1V
Output Capacitance	—	C_{OUT}	—	12	pF	V_{IN} = 0V; Tamb = 25°C; f = 1 MHz (Note 2)
Power Suppy Current, Active	TTL input	I_{CC}	—	30	mA	f = 5 MHz (Note 1) Vcc = 5.5V;
Power Supply Current, Standby	TTL input TTL input CMOS input	$I_{CC(S)TTL}$ $I_{CC(S)TTL}$ $I_{CC(S)CMOS}$	—	2 3 100	mA mA µA	$\overline{CE}$ = V_{IH} (0°C to 70°C) $\overline{CE}$ = V_{IH} (-40°C to 85°C) $\overline{CE}$ = Vcc-0.3 to Vcc+1

Note: (1) AC power supply current above 5 MHz: 2 mA/MHz.
(2) Not 100% tested.

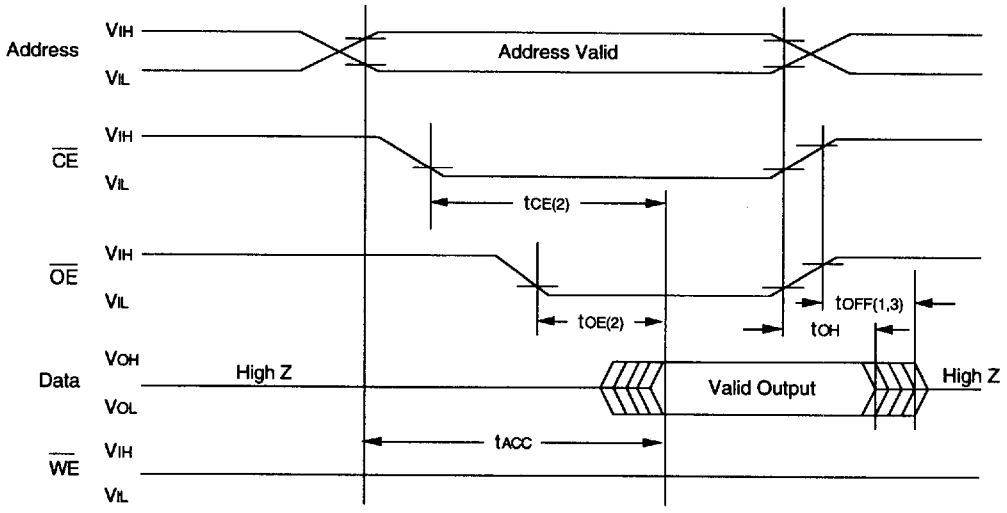
READ OPERATION
AC Characteristics

AC Testing Waveform: V_{IH} = 2.4V; V_{IL} = 0.45V; V_{OH} = 2.0V; V_{OL} = 0.8V
Output Load: 1 TTL Load + 100 pF
Input Rise and Fall Times: 20 ns
Ambient Temperature: Commercial (C): Tamb = 0°C to 70°C
Industrial (I): Tamb = -40°C to 85°C

Parameter	Sym	28C64A-15		28C64A-20		28C64A-25		Units	Conditions
		Min	Max	Min	Max	Min	Max		
Address to Output Delay	t_{ACC}	—	150	—	200	—	250	ns	$\overline{OE}$ = $\overline{CE}$ = V_{IL}
$\overline{CE}$ to Output Delay	t_{CE}	—	150	—	200	—	250	ns	$\overline{OE}$ = V_{IL}
$\overline{OE}$ to Output Delay	t_{OE}	—	70	—	80	—	100	ns	$\overline{CE}$ = V_{IL}
$\overline{CE}$ or $\overline{OE}$ High to Output Float	t_{OFF}	0	50	0	55	0	70	ns	Note 1
Output Hold from Address, $\overline{CE}$ or $\overline{OE}$, whichever occurs first.	t_{OH}	0	—	0	—	0	—	ns	Note 1

Note: (1) Not 100% tested.

READ WAVEFORMS



Notes: (1) t_{OFF} is specified for $\overline{OE}$ or $\overline{CE}$, whichever occurs first
(2) $\overline{OE}$ may be delayed up to t_{CE} - t_{OE} after the falling edge of $\overline{CE}$ without impact on t_{CE}
(3) This parameter is sampled and is not 100% tested

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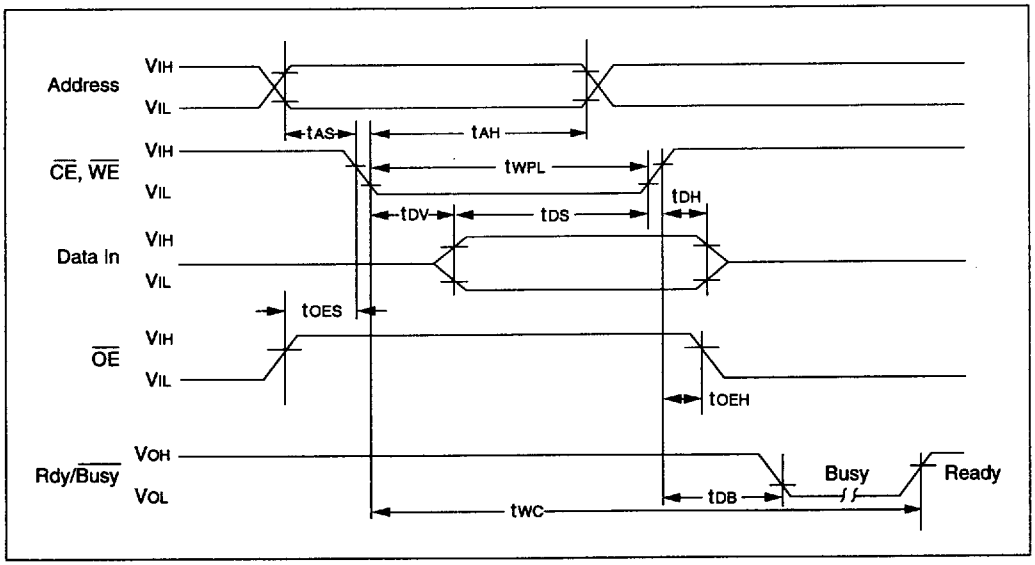
BYTE WRITE AC Characteristics

AC Testing Waveform: V_{IH} = 2.4V and V_{IL} = 0.45V; V_{OH} = 2.0V; V_{OL} = 0.8V
Output Load: 1 TTL Load + 100 pF
Input Rise/Fall Times: 20 ns
Ambient Temperature: Commercial (C): Tamb = 0°C to 70°C
Industrial (I): Tamb = -40°C to 85°C

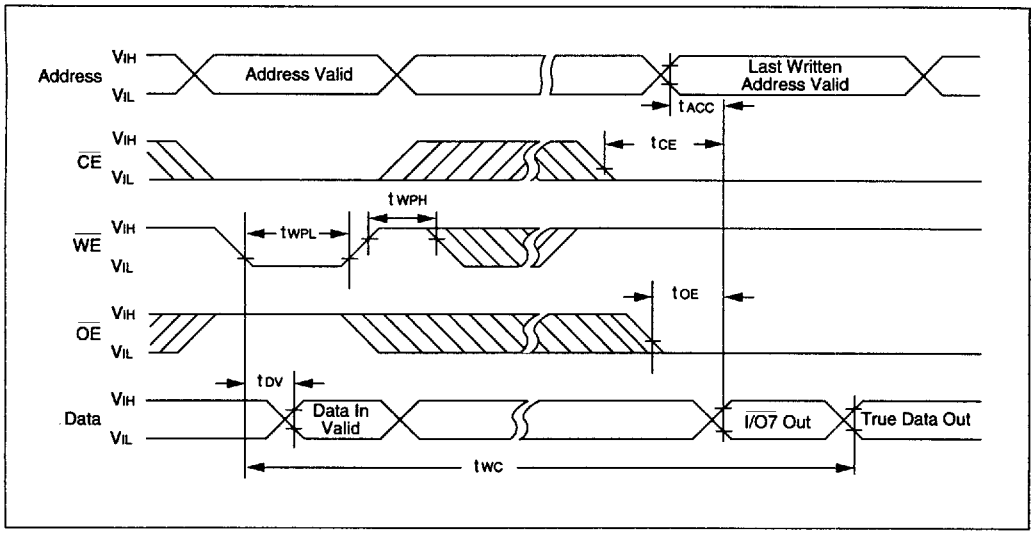
Parameter	Symbol	Min	Max	Units	Remarks
Address Set-Up Time	t_{AS}	10	—	ns	
Address Hold Time	t_{AH}	50	—	ns	
Data Set-Up Time	t_{DS}	50	—	ns	
Data Hold Time	t_{DH}	10	—	ns	
Write Pulse Width	t_{WPL}	100	—	ns	Note 1
Write Pulse High Time	t_{WPH}	50	—	ns	
$\overline{OE}$ Hold Time	t_{OEH}	10	—	ns	
$\overline{OE}$ Set-Up Time	t_{OES}	10	—	ns	
Data Valid Time	t_{DV}	—	1000	ns	Note 2
Time to Device Busy	t_{DB}	2	50	ns	
Write Cycle Time (28C64A)	t_{WC}	—	1	ms	0.5 ms typical
Write Cycle Time (28C64AF)	t_{WC}	—	200	µs	100 µs typical

Note: (1) A write cycle can be initiated be $\overline{CE}$ or $\overline{WE}$ going low, whichever occurs last. The data is latched on the positive edge of $\overline{CE}$ or $\overline{WE}$, wichever occurs first.
(2) Data must be valid within 1000ns max. after a write cycle is initiated and must be stable at least until t_{DH} after the positive edge of $\overline{WE}$ or $\overline{CE}$, whichever occurs first.

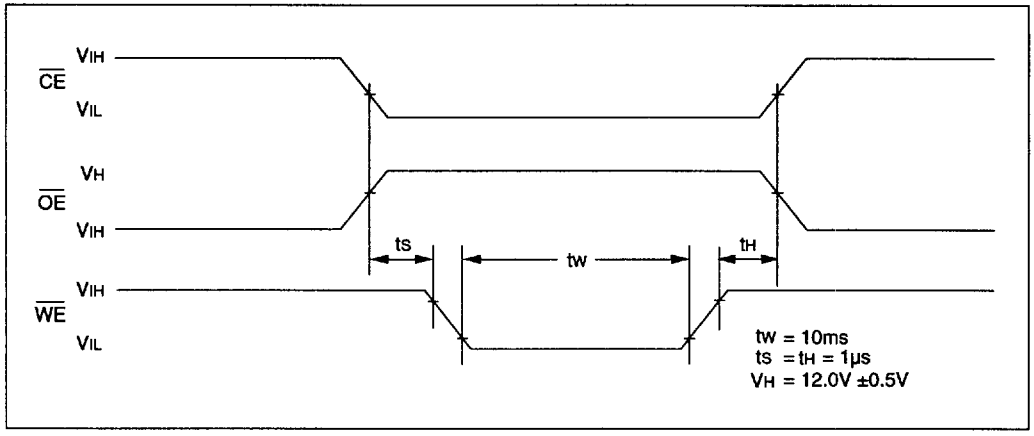
PROGRAMMING WAVEFORMS



DATA POLLING WAVEFORMS



CHIP CLEAR WAVEFORMS



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SUPPLEMENTARY CONTROL						
Mode	**CE**	**OE**	**WE**	**A9**	**Vcc**	**I/Oi**
Chip Clear	VIL	VH	VIL	X	Vcc	
Extra Row Read	VIL	VIL	VIH	A9 = VH	Vcc	Data Out
Extra Row Write	*	VIH	*	A9 = VH	Vcc	Data In
Note: VH = 12.0V ±0.5V		* Pulsed per programming waveforms.				

DEVICE OPERATION

The Microchip Technology Inc. 28C64A has four basic modes of operation—read, standby, write inhibit, and byte write—as outlined in the following table.

Operation Mode	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O	Rdy/$\overline{Busy}$ (1)
Read	L	L	H	DOUT	H
Standby	H	X	X	High Z	H
Write Inhibit	H	X	X	High Z	H
Write Inhibit	X	L	X	High Z	H
Write Inhibit	X	X	H	High Z	H
Byte Write	L	H	L	DIN	L
Byte Clear	Automatic Before Each "Write"				

Note: (1) Open drain output.
(2) X = Any TTL level.

Read Mode

The 28C64A has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip enable ($\overline{CE}$) is the power control and should be used for device selection. Output Enable ($\overline{OE}$) is the output control and is used to gate data to the output pins independent of device selection. Assuming that addresses are stable, address access time (tACC) is equal to the delay from $\overline{CE}$ to output (tCE). Data is available at the output tOE after the falling edge of $\overline{OE}$, assuming that $\overline{CE}$ has been low and addresses have been stable for at least tACC-tOE.

Standby Mode

The 28C64A is placed in the standby mode by applying a high signal to the $\overline{CE}$ input. When in the standby mode, the outputs are in a high impedance state, independent of the $\overline{OE}$ input.

Data Protection

In order to ensure data integrity, especially during critical power-up and power-down transitions, the following enhanced data protection circuits are incorporated:

First, an internal Vcc detect (3.3 volts typical) will inhibit the initiation of non-volatile programming operation when Vcc is less than the Vcc detect circuit trip.

Second, there is a $\overline{WE}$ filtering circuit that prevents $\overline{WE}$ pulses of less than 10 ns duration from initiating a write cycle.

Third, holding $\overline{WE}$ or $\overline{CE}$ high or $\overline{OE}$ low, inhibits a write cycle during power-on and power-off (Vcc).

Write Mode

The 28C64A has a write cycle similar to that of a Static RAM. The write cycle is completely self-timed and initiated by a low going pulse on the $\overline{WE}$ pin. On the falling edge of WE, the address information is latched. On rising edge, the data and the control pins ($\overline{CE}$ and $\overline{OE}$) are latched. The Ready/Busy pin goes to a logic low level indicating that the 28C64A is in a write cycle which signals the microprocessor host that the system bus is free for other activity. When Ready/Busy goes back to a high, the 28C64A has completed writing and is ready to accept another cycle.

$\overline{Data}$ Polling

The 28C64A features $\overline{Data}$ polling to signal the completion of a byte write cycle. During a write cycle, an attempted read of the last byte written results in the data complement of I/O7 (I/O0 to I/O6 are indeterminable). After completion of the write cycle, true data is available. Data polling allows a simple read/compare operation to determine the status of the chip eliminating the need for external hardware.

Electronic Signature for Device Identification

An extra row of 32 bytes of EEPROM memory is available to the user for device identification. By raising A9 to 12V ±0.5V and using address locations 1FE0 to 1FFF, the additional bytes can be written to or read from in the same manner as the regular memory array.

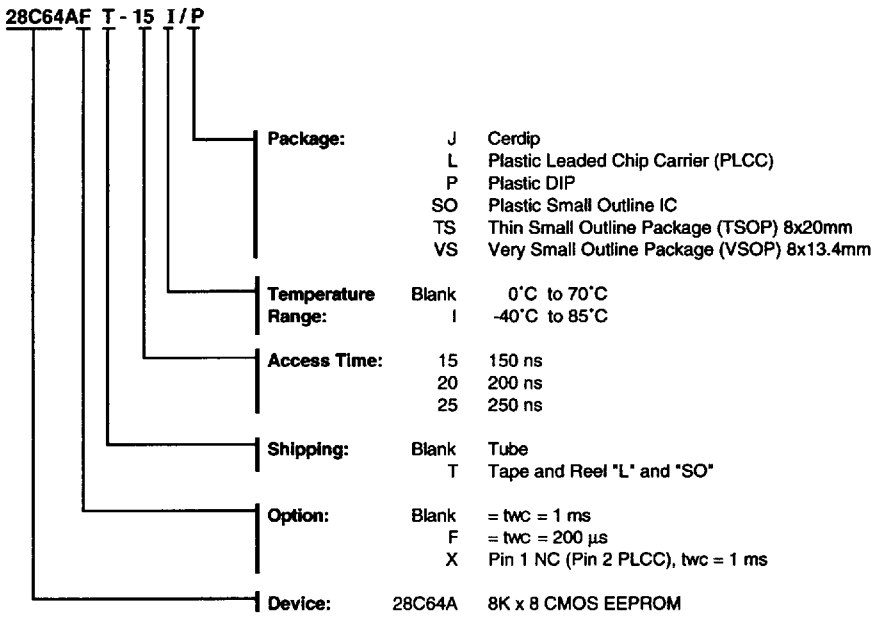
Chip Clear

All data may be cleared to 1's in a chip clear cycle by raising $\overline{OE}$ to 12 volts and bringing the $\overline{WE}$ and $\overline{CE}$ low. This procedure clears all data, except for the extra row.

SALES AND SUPPORT

To order or to obtain information, e.g., on pricing or delivery, please use the listed part numbers, and refer to the factory or the listed sales offices.

PART NUMBERS



MICROCHIP

PACKAGING

Commercial/Industrial Outlines and Parameters

COMMERCIAL AND INDUSTRIAL PARTS

Part Number Suffix Designations:

XXXXXXXXXX - XX X / XX XXX

Examples:

27C256T-15I/J
PIC16C54-RCI/SO

ROM Code or Special Requirements

Case Outline

D	= Ceramic
J	= Cerdip (with window if EPROM) - all product except Microcontrollers
K	= LCC (Ceramic Leadless Chip Carrier, not thermally enhanced)
L	= PLCC (Plastic Leaded Chip Carrier)
P	= Plastic
S	= Die in Waffle Pack
W	= Die in Wafer Form
CB	= COB (Chip-On-Board)
JN	= Cerdip, no window - for Microcontrollers only
JW	= Cerdip, windowed - for Microcontrollers only
PQ	= PQFP
SJ	= Skinny Cerdip
SL	= 14-Lead Small Outline .150 mil
SM	= Small Outline .207 mil
SN	= Small Outline .150 mil
SO	= Small Outline .300 mil
SP	= Skinny Plastic Carrier
SS	= Shrink Small Outline Package
TS	= Thin Small Outline (TSOP) 8mm x 20mm
VS	= Very Small Outline (VSOP) 8 x 13mm

Process Temperature

Blank	= 0°C to +70°C
I	= -40°C to +85°C
E	= -40°C to +125°C

Speed (EPROM / High Density EEPROM)	**Frequency**	**Crystal Frequency Designator for PIC16/17 Microcontrollers**
-55 = 55 ns	Blank = 20.5 MHz	LP = 4 µs - Low Power
-70 = 70 ns	-14 = 14.4 MHz	RC = 2 µs - Resistor Capacitor
-90 = 90 ns	-25 = 25.6 MHz	XT = 1 µs - Crystal
-10 = 100 ns	-32 = 32.8 MHz	HS = 20 MHz - High Speed Crystal
-12 = 120 ns		-10 = 10 MHz - High Speed Crystal
-15 = 150 ns		-04 = 4 MHz - Crystal or RC
-17 = 170 ns		-16 = 16 MHz - High Speed Crystal
-20 = 200 ns		-20 = 20 MHz - High Speed Crystal
-25 = 250 ns		-25 = 25 MHz - High Speed Crystal

OPTION

-	= twc = 1 ms
F	= twc = 200 µs
X	= Rotated pinout
T	= Tape and Reel

Device Type (Up To 10 Digits)

C	= Indicates CMOS
LC	= Indicates Low Power CMOS
AA	= 1.8V
LV	= Low Voltage
HC	= High Speed
LCS	= Low Power Security

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16-Lead, Side Brazed, 300 mil 11-1-4
18-Lead, Side Brazed, 300 mil 11-1-5
22-Lead, Side Brazed, 400 mil 11-1-6
24-Lead, Side Brazed, 600 mil 11-1-7
24-Lead, Side Brazed, 600 mil, Window 11-1-8
28-Lead, Side Brazed, 600 mil 11-1-9
28-Lead, Side Brazed, 600 mil, Window 11-1-10
40-Lead, Side Brazed, 600 mil 11-1-11
40-Lead, Side Brazed, 600 mil, Window 11-1-12
48-Lead, Side Brazed, 600 mil 11-1-13

B. Ceramic Cerdip Dual In-line Package ("J, JW, SJ" Case Outlines)

Symbol List for Cerdip Dual In-Line Package Parameters 11-1-14
8-Lead, Cerdip, 300 mil 11-1-15
16-Lead, Cerdip, 300 mil 11-1-16
18-Lead, Cerdip, 300 mil 11-1-17
18-Lead, Cerdip, 300 mil, Window 11-1-18
22-Lead, Cerdip, 400 mil 11-1-19
24-Lead, Cerdip, 300 mil 11-1-20
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C. Ceramic Flatpack

Symbol List for Ceramic Flatpack Package Parameters 11-1-28
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E. Ceramic Leaded Chip Carrier (Surface Mount Package, "JL" Case Outlines)

Symbol List for Ceramic Leaded Chip Carrier Package Parameters 11-1-38
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84-Lead (Window) 11-1-40

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Symbol List for Plastic Dual In-Line Package Parameters 11-2-1
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14-Lead, 300 mil 11-2-3
16-Lead, 300 mil 11-2-4
18-Lead, 300 mil 11-2-5
22-Lead, 400 mil 11-2-6
24-Lead, 600 mil 11-2-7
24-Lead, 300 mil 11-2-8
28-Lead, 300 mil 11-2-9
28-Lead, 600 mil 11-2-10
40-Lead, 600 mil 11-2-11
48-Lead, 600 mil 11-2-12

B. Plastic Leaded Chip Carrier (Surface Mount, "L" Case Outlines)

Symbol List for Plastic Leaded Chip Carrier Package Parameters 11-2-13
28-Lead (Square) 11-2-14
32-Lead (Rectangle) 11-2-15
44-Lead (Square) 11-2-16
68-Lead (Square) 11-2-17
84-Lead (Square) 11-2-18

C. Plastic Small Outline (SOIC) (Surface Mount, "SN, SL, SM, SW, SO" Case Outlines)

Symbol List for Plastic Small Outline Package Parameters 11-2-19
8-Lead, 150 mil (Body) 11-2-20
8-Lead, 200 mil (Body) 11-2-21
14-Lead, 150 mil (Body) 11-2-22
18-Lead, 300 mil (Body) 11-2-23
24-Lead, 300 mil (Body) 11-2-24
28-Lead, 300 mil (Body) 11-2-25
28-Lead, 330 mil (Body) 11-2-26

D. Plastic Shrink Small Outline (SSOP) (Surface Mount "SS" Case Outlines)

Symbol List for Plastic Shrink Small Outline Package Parameters 11-2-27
20-Lead, 209 mil Body (5.30mm) 11-2-28
28-Lead, 209 mil Body (5.30mm) 11-2-29

E. Plastic Thin Small Outline (TSOP) and Very Small Outline (VSOP) (Surface Mount, "TS" and "VS" Case Outlines)

Symbol List for Thin and Very Small Outline Package Parameters 11-2-30
28-Lead, (8 x 20mm) TSOP Type I 11-2-31
28-Lead, (8 x 13mm) VSOP Type I 11-2-32

F. Plastic Metric Quad Flatpack (MQFP) (Surface Mount, "PQ" Case Outlines)

Symbol List for Plastic Metric Quad Flatpack Package Parameters 11-2-33
44-Lead, (10x10mm) Body 1.6/0.15mm 11-2-34